Abstract

A method for producing a wafer comprising a silicon single crystal substrate having a front and a back side and a layer of SiGe deposited on the front side

A method for producing a wafer comprising a silicon single crystal substrate having a front and a back side and a layer of SiGe deposited on the front side, the method comprising steps in the following order:
Simultaneously polishing the front and the back side of the silicon single crystal substrate;
depositing a stress compensating layer on the back side of the silicon single crystal substrate;
polishing the front side of the silicon single crystal substrate;
cleaning the silicon single crystal substrate having the stress compensating layer deposited on the back side; and
depositing a fully or partially relaxed layer of SiGe on the front side of the silicon single crystal substrate.

Figure 2